

13. The method of claim 10 wherein the nitride layer, the polysilicon layer and the thermal oxide layer are completely removed following the formation of the oxide isolation elements.

14. The method of claim 10 wherein the plurality of trenches are approximately the same width.

15. The method of claim 10 wherein the plurality of trenches are of varying widths.

16. The method of claim 10 wherein contact is made to the substrate through one or more of the polysilicon filled trenches.

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